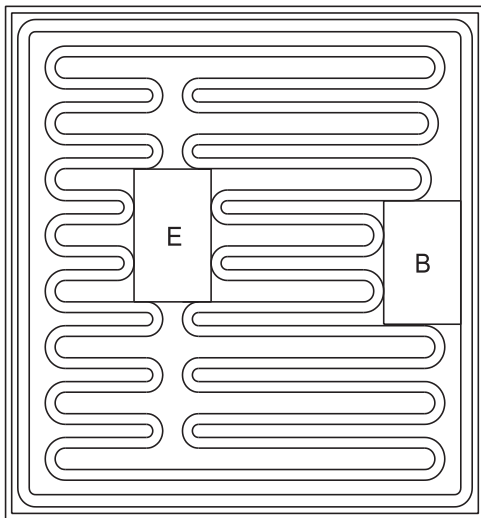


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	82 x 82 MILS
Die Thickness	11 MILS
Base Bonding Pad Area	13.2 x 19.7 MILS
Emitter Bonding Pad Area	13.2 x 21.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

**GEOMETRY**



BACKSIDE COLLECTOR R0

**GROSS DIE PER 4 INCH WAFER**

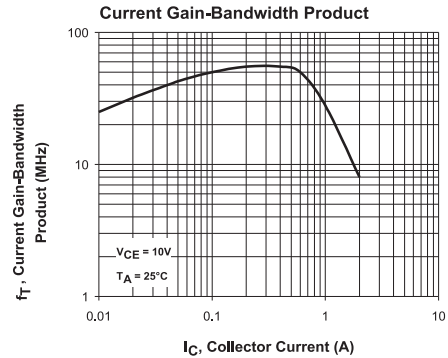
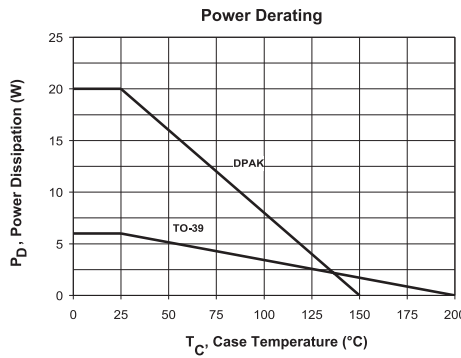
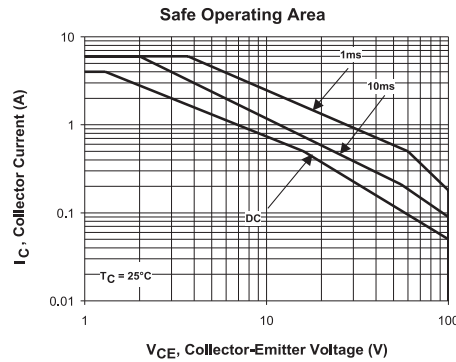
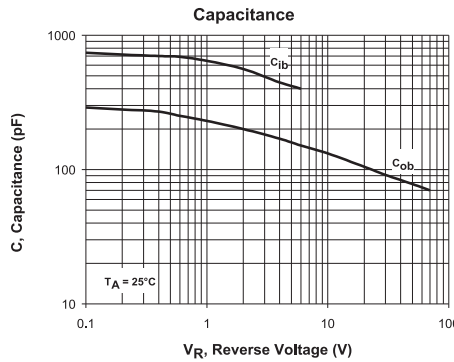
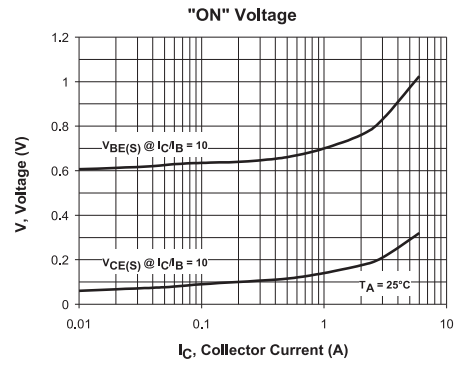
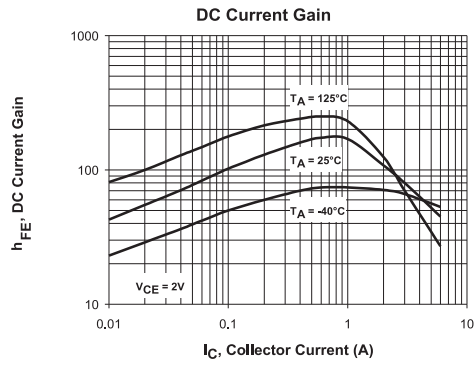
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**PRINCIPAL DEVICE TYPES**

2N5336  
2N5337  
2N5338  
2N5339  
2N5427  
2N5428  
2N5429  
2N5430  
D44H11  
CJD44H11

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R2 (21-September 2003)



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